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# 1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	60	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	120	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	120	A
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	480	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	40	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	28.5	A
$I_{DM}^{(2)(3)}$	Drain current (pulsed)	160	A
$E_{AS}$	Single pulse avalanche energy (starting $T_J = 25\text{ }^\circ\text{C}$ , $I_{AS} = 20\text{ A}$ )	900	mJ
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	188	W
$P_{TOT}^{(3)}$	Total dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$T_J$	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
	Storage temperature range		

**Notes:**

<sup>(1)</sup>This value is rated according to  $R_{thj-c}$ .

<sup>(2)</sup>Pulse width limited by safe operating area.

<sup>(3)</sup>This value is rated according to  $R_{thj-pcb}$ .

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^\circ\text{C/W}$
$R_{thj-case}$	Thermal resistance junction-case	0.8	$^\circ\text{C/W}$

**Notes:**

<sup>(1)</sup>When mounted on FR-4 board of 1 inch<sup>2</sup>, 2oz Cu,  $t < 10\text{ s}$ .

## 2 Electrical characteristics

(T<sub>C</sub> = 25 °C unless otherwise specified)

**Table 4: On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source breakdown voltage	I <sub>D</sub> = 1 mA, V <sub>GS</sub> = 0 V	60			V
I <sub>DSS</sub>	Zero gate voltage drain current	V <sub>GS</sub> = 0 V V <sub>DS</sub> = 60 V			1	μA
I <sub>GSS</sub>	Gate-body leakage current	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V			100	nA
V <sub>GS(th)</sub>	Gate threshold voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2		4	V
R <sub>DS(on)</sub>	Static drain-source on-resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		1.2	1.4	mΩ

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C <sub>iss</sub>	Input capacitance	V <sub>DS</sub> = 25 V, f = 1 MHz, V <sub>GS</sub> = 0 V	-	6500	-	pF
C <sub>oss</sub>	Output capacitance		-	3200	-	pF
C <sub>rss</sub>	Reverse transfer capacitance		-	230	-	pF
Q <sub>g</sub>	Total gate charge	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 40 A, V <sub>GS</sub> = 0 to 10 V (see <a href="#">Figure 14: "Test circuit for gate charge behavior"</a> )	-	98	-	nC
Q <sub>gs</sub>	Gate-source charge		-	38	-	nC
Q <sub>gd</sub>	Gate-drain charge		-	28	-	nC

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t <sub>d(on)</sub>	Turn-on delay time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 20 A, R <sub>G</sub> = 4.7 Ω, V <sub>GS</sub> = 10 V (see <a href="#">Figure 13: "Test circuit for resistive load switching times"</a> and <a href="#">Figure 18: "Switching time waveform"</a> )	-	41	-	ns
t <sub>r</sub>	Rise time		-	45	-	ns
t <sub>d(off)</sub>	Turn-off delay time		-	68	-	ns
t <sub>f</sub>	Fall time		-	35	-	ns

**Table 7: Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V <sub>SD</sub> <sup>(1)</sup>	Forward on voltage	I <sub>SD</sub> = 40 A, V <sub>GS</sub> = 0 V	-		1.2	V
t <sub>rr</sub>	Reverse recovery time	I <sub>D</sub> = 40 A, di/dt = 100 A/μs V <sub>DD</sub> = 48 V (see <a href="#">Figure 15: "Test circuit for inductive load switching and diode recovery times"</a> )	-	69		ns
Q <sub>rr</sub>	Reverse recovery charge		-	103		nC
I <sub>RRM</sub>	Reverse recovery current		-	3		A

**Notes:**

<sup>(1)</sup>Pulsed: pulse duration = 300 μs, duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2: Safe operating area

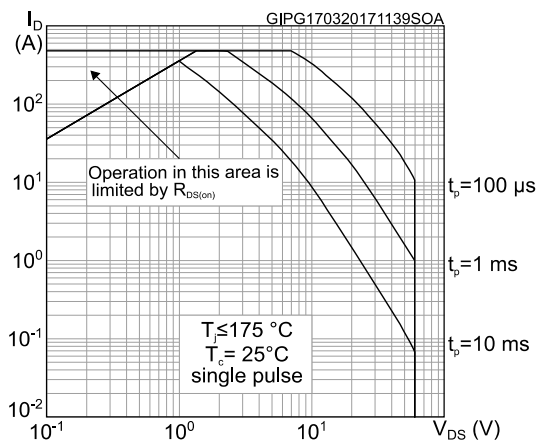


Figure 3: Thermal impedance

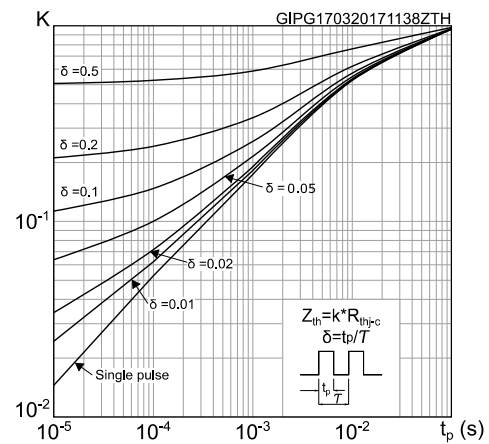


Figure 4: Output characteristics

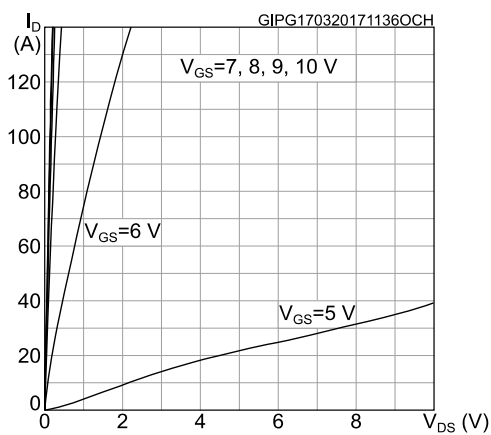


Figure 5: Transfer characteristics

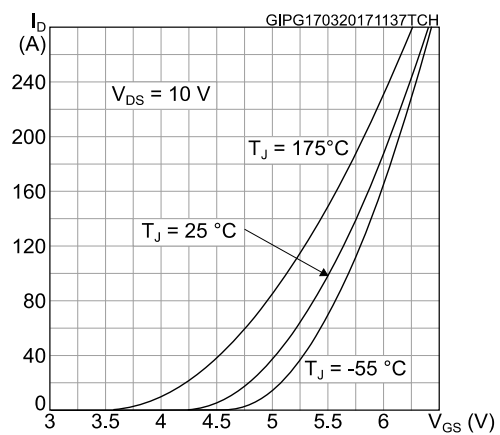


Figure 6: Static drain-source on-resistance

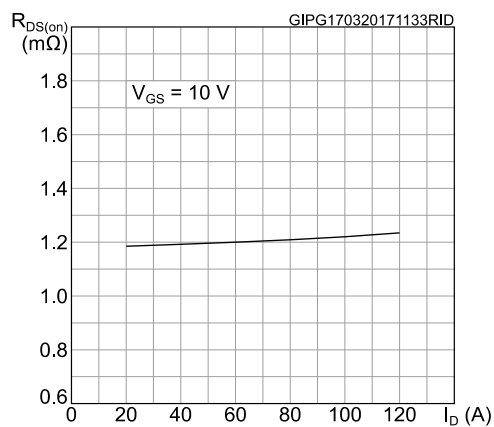


Figure 7: Gate charge vs gate-source voltage

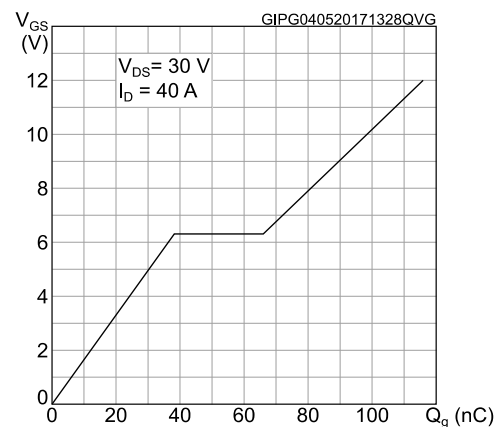


Figure 8: Capacitance variations

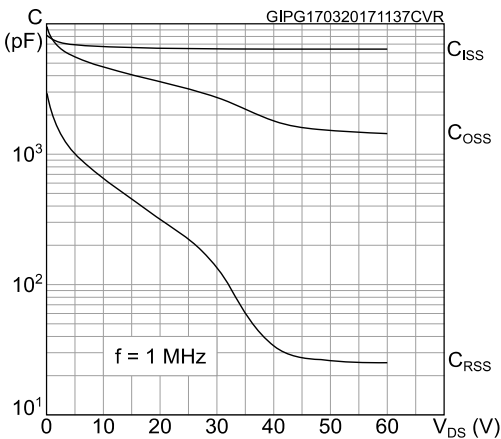


Figure 9: Normalized gate threshold voltage vs temperature

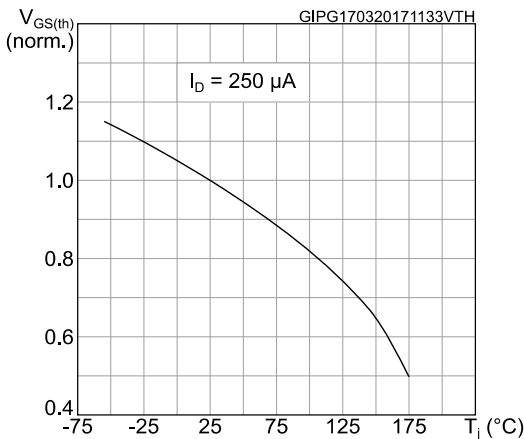


Figure 10: Normalized on-resistance vs temperature

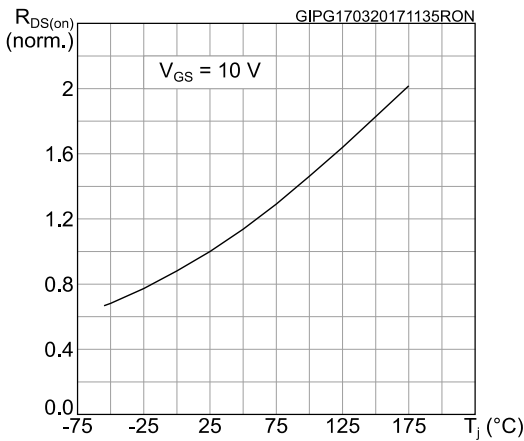


Figure 11: Source-drain diode forward characteristics

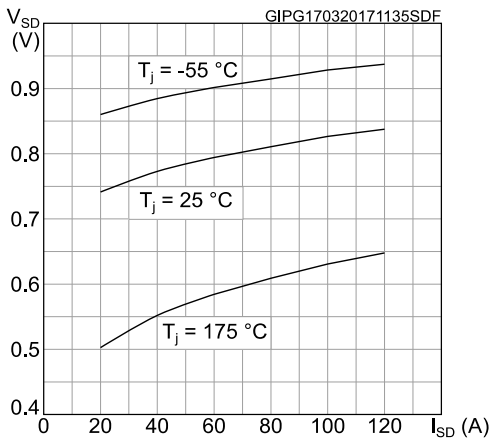
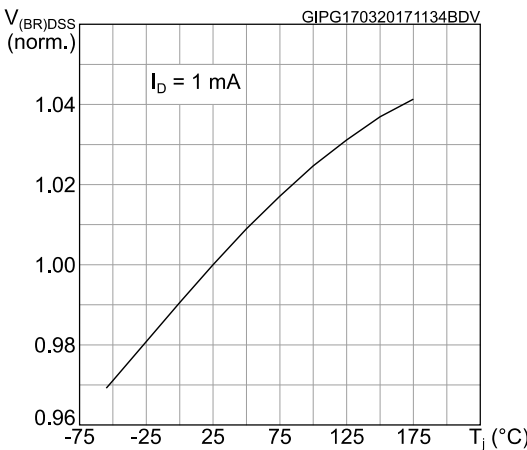
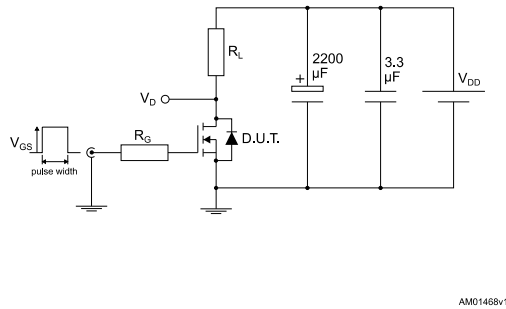


Figure 12: Normalized  $V_{(BR)DSS}$  vs temperature

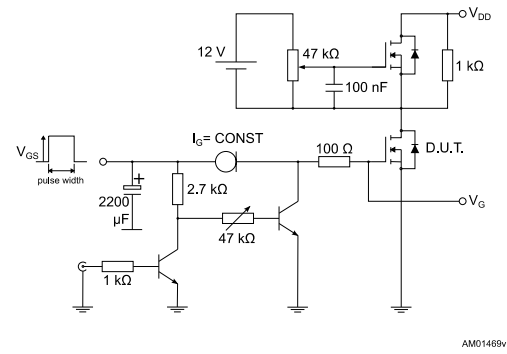


### 3 Test circuits

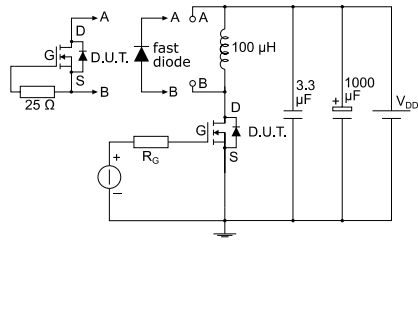
**Figure 13: Test circuit for resistive load switching times**



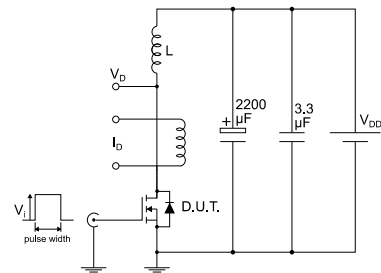
**Figure 14: Test circuit for gate charge behavior**



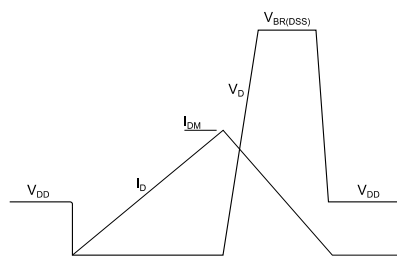
**Figure 15: Test circuit for inductive load switching and diode recovery times**



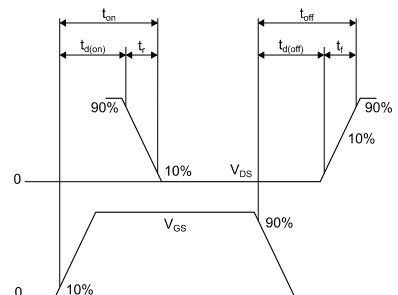
**Figure 16: Unclamped inductive load test circuit**



**Figure 17: Unclamped inductive waveform**



**Figure 18: Switching time waveform**

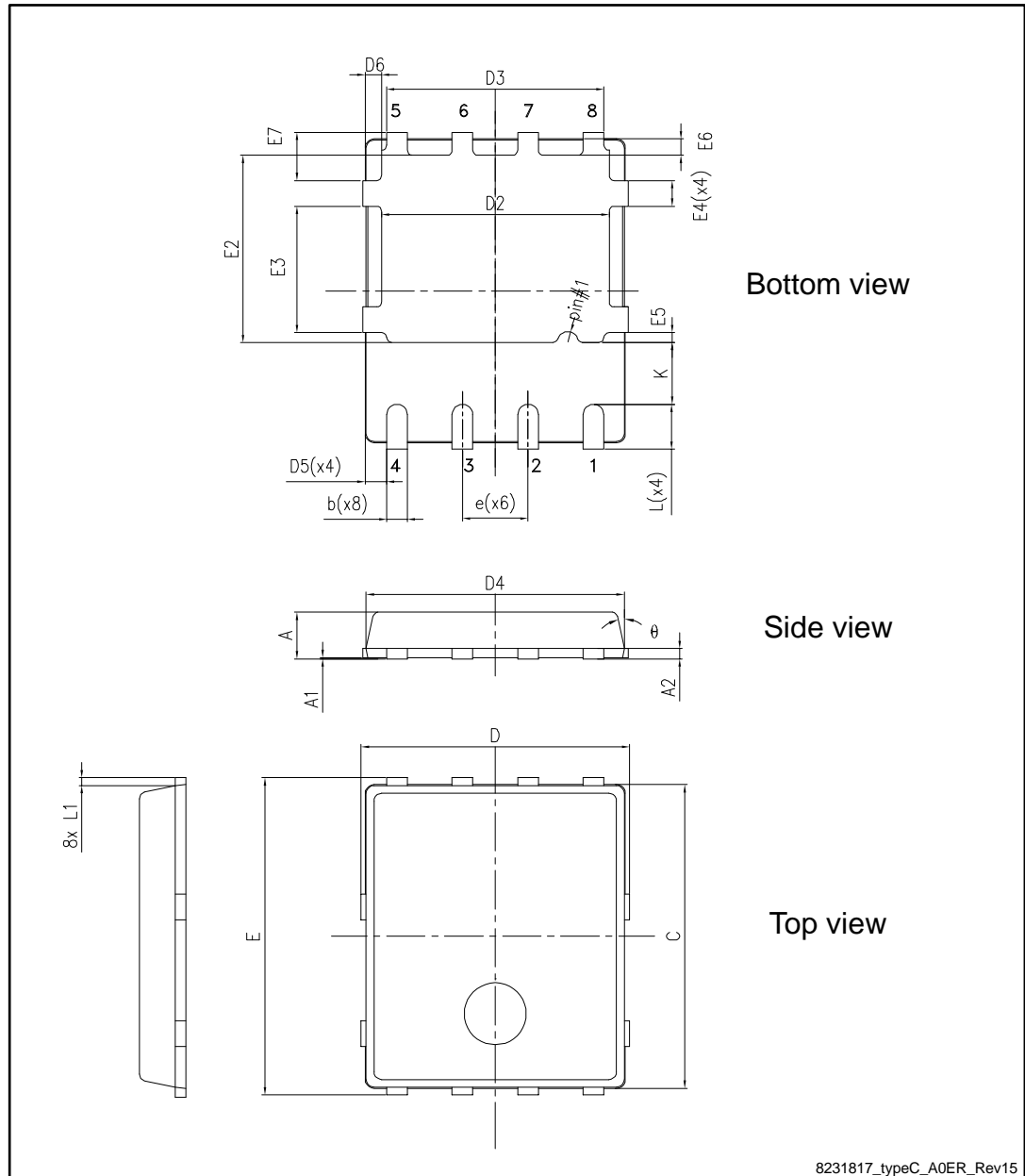


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 PowerFLAT 5x6 type C package mechanical data

Figure 19: PowerFLAT™ 5x6 type C package outline







4.2 PowerFLAT 5x6 packaging information

Figure 21: PowerFLAT™ 5x6 tape (dimensions are in mm)

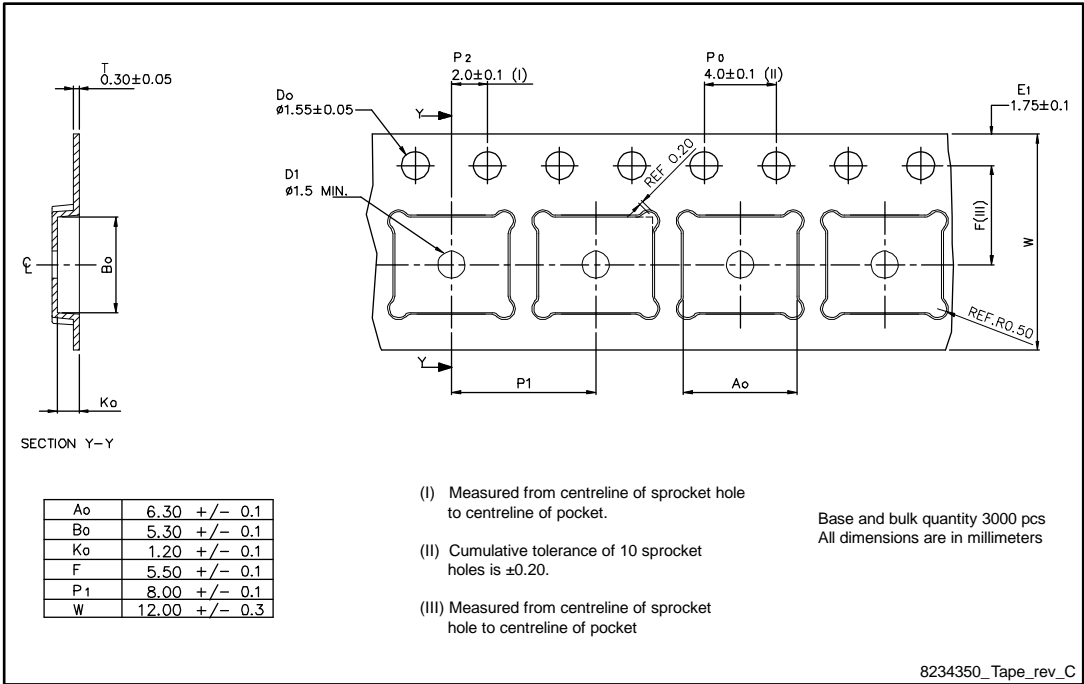


Figure 22: PowerFLAT™ 5x6 package orientation in carrier tape

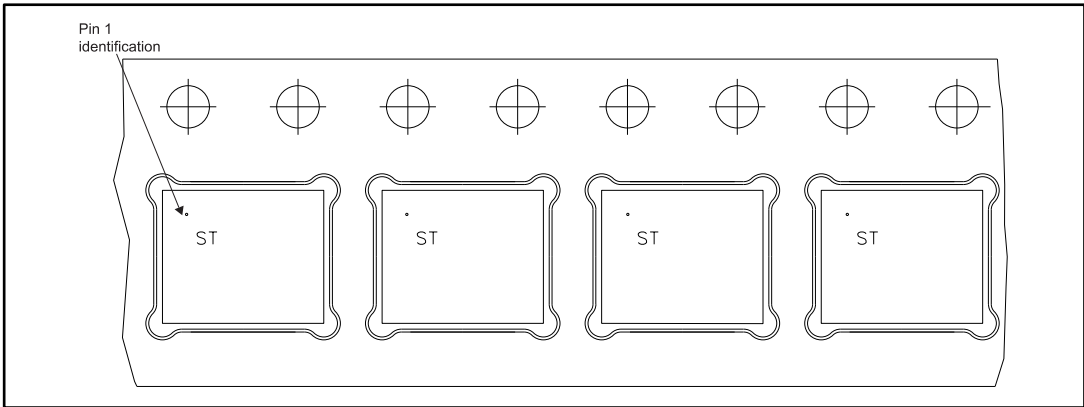
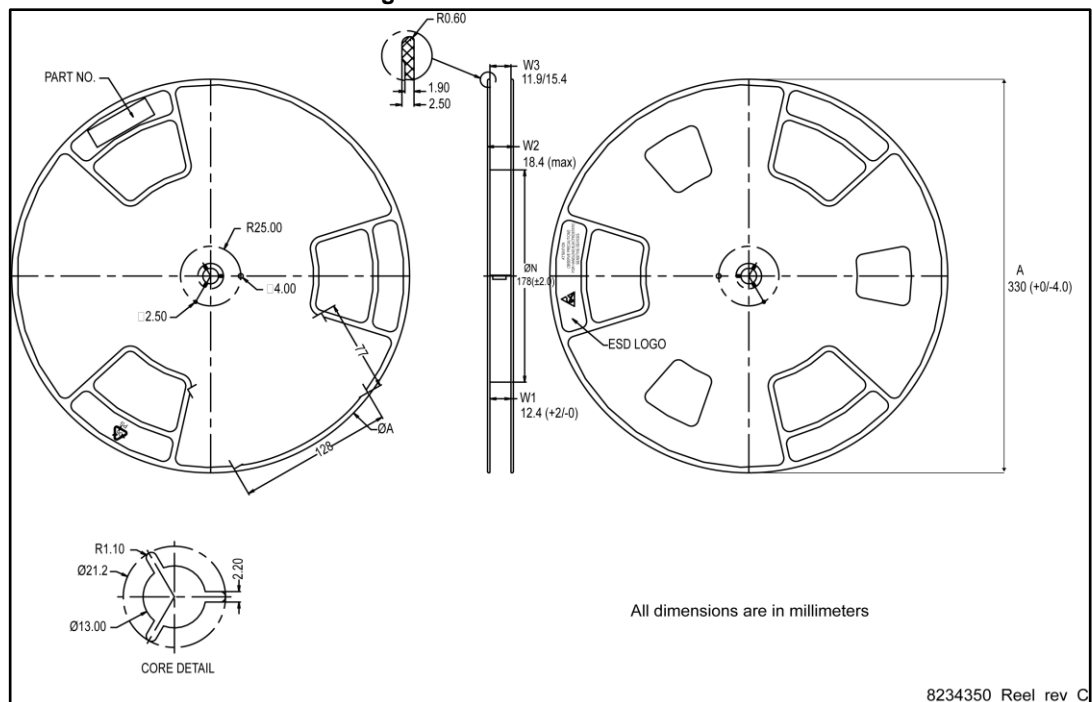


Figure 23: PowerFLAT™ 5x6 reel



## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
13-Jun-2014	1	First release.
22-Sep-2014	2	Updated title, features and description in cover page. Updated <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "On /off states"</i> , <i>Table 5: "Dynamic"</i> , <i>Table 6: "Switching times"</i> and <i>Table 7: "Source-drain diode"</i> . Added <i>Section 3: "Electrical characteristics (curves)"</i> .
14-Jan-2015	3	Document status promoted from preliminary to production data.
02-May-2017	4	Modified title and features table on cover page. Modified <i>Table 2: "Absolute maximum ratings"</i> , <i>Table 4: "On /off states"</i> , <i>Table 5: "Dynamic"</i> , <i>Table 6: "Switching times"</i> and <i>Table 7: "Source-drain diode"</i> . Modified <i>Section 2.1: "Electrical characteristics (curves)"</i> . Minor text changes.

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